

SPI35N10 Information



For Reference Only

Part Number SPI35N10

Manufacturer Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 100V 35A I2PAK

Package TO-262-3 Long Leads, I2Pak, TO-262AA

For the pricing/inventory/lead time, please contact

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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SPI35N10 Specifications

Manufacturer Part Number SPI35N10 Manufacturer Infineon Technologies Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-262-3 Long Leads, 12Pak, TO-262AA Series SIPMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 35A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 83µA Gate Charge (Qg) (Max) @ Vgs 55nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1570pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 150W (Tc) Rds On (Max) @ Id, Vgs 44 mOhm @ 26.4A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO262-3-1 Package / Case TO-262-3 Long Leads, 12Pak, TO-262AA Report errors?		
CategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-262-3 Long Leads, 12Pak, TO-262AASeriesSIPMOS?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C35A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 83μAGate Charge (Qg) (Max) @ Vgs65nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1570pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)150W (Tc)Rds On (Max) @ Id, Vgs44 mOhm @ 26.4A, 10VOperating Temperature-55°C ~ 175°C (TI)Mounting TypeThrough HoleSupplier Device PackagePG-TO262-3-1Package / CaseTO-262-3 Long Leads, 12Pak, TO-262AA	Manufacturer Part Number	SPI35N10
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Package TO-262-3 Long Leads, 12Pak, TO-262AA Series SIPMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 35A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 83μA Gate Charge (Qg) (Max) @ Vgs 65nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1570pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 150W (Tc) Rds On (Max) @ Id, Vgs 44 mOhm @ 26.4A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO262-3-1 Package / Case TO-262-3 Long Leads, 12Pak, TO-262AA	Category	Discrete Semiconductor Products
SeriesSIPMOS?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C35A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 83μAGate Charge (Qg) (Max) @ Vgs65nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1570pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)150W (Tc)Rds On (Max) @ Id, Vgs44 mOhm @ 26.4A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO262-3-1Package / CaseTO-262-3 Long Leads, 12Pak, TO-262AA		Transistors - FETs, MOSFETs - Single
FET Type Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 35A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 44 mOhm @ 26.4A, 10V Operating Temperature Supplier Device Package PG-TO262-3-1 Package / Case N-Centinuous Drain (Id) @ 25°C 35A (Tc) 4V @ 83µA 4V @ 83µA 4DV 4DV 4DV 4DV 4DV 4DV 4DV 4D	Package	TO-262-3 Long Leads, I2Pak, TO-262AA
Technology Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 35A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 83µA Gate Charge (Qg) (Max) @ Vgs 65nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1570pF @ 25V Vgs (Max) ##ET Feature - Power Dissipation (Max) 150W (Tc) Rds On (Max) @ Id, Vgs 44 mOhm @ 26.4A, 10V Operating Temperature ##Ohm @ 26.4A, 10V Operating Type Through Hole Supplier Device Package PG-TO262-3-1 Package / Case ##Osofree (Max) (Max	Series	SIPMOS?
Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C35A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 83μAGate Charge (Qg) (Max) @ Vgs65nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1570pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)150W (Tc)Rds On (Max) @ Id, Vgs44 mOhm @ 26.4A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO262-3-1Package / CaseTO-262-3 Long Leads, I2Pak, TO-262AA	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Supplier Device Package Package / Case 35A (Tc) 10V 4V @ 83μA 65nC @ 10V 1570pF @ 25V 25V 25V 25V 26V 76C (TJ) Through Hole Supplier Device Package PG-TO262-3-1 TO-262-3 Long Leads, 12Pak, TO-262AA	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 83μAGate Charge (Qg) (Max) @ Vgs65nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1570pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)150W (Tc)Rds On (Max) @ Id, Vgs44 mOhm @ 26.4A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO262-3-1Package / CaseTO-262-3 Long Leads, 12Pak, TO-262AA	Drain to Source Voltage (Vdss)	100V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 1570pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) I50W (Tc) Rds On (Max) @ Id, Vgs 44 mOhm @ 26.4A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO262-3-1 Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Current - Continuous Drain (Id) @ 25°C	35A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 1570pF @ 25V Vgs (Max) ±20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 44 mOhm @ 26.4A, 10V Operating Temperature John Charles (TJ) Mounting Type Through Hole Supplier Device Package PG-TO262-3-1 Package / Case For Capacitance (Ciss) (Max) @ Vds 1570pF @ 25V 420V Through Hole FET Feature -50°C ~ 175°C (TJ) Through Hole Through Hole Through Hole	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) E20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 44 mOhm @ 26.4A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO262-3-1 Package / Case TO-262-3 Long Leads, 12Pak, TO-262AA	Vgs(th) (Max) @ Id	4V @ 83μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)150W (Tc)Rds On (Max) @ Id, Vgs44 mOhm @ 26.4A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO262-3-1Package / CaseTO-262-3 Long Leads, I2Pak, TO-262AA	Gate Charge (Qg) (Max) @ Vgs	65nC @ 10V
FET Feature - 150W (Tc) Rds On (Max) @ Id, Vgs	Input Capacitance (Ciss) (Max) @ Vds	1570pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 44 mOhm @ 26.4A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO262-3-1 Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs44 mOhm @ 26.4A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO262-3-1Package / CaseTO-262-3 Long Leads, I2Pak, TO-262AA	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO262-3-1 Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Power Dissipation (Max)	150W (Tc)
Mounting Type Through Hole Supplier Device Package PG-TO262-3-1 Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Rds On (Max) @ Id, Vgs	44 mOhm @ 26.4A, 10V
Supplier Device Package PG-TO262-3-1 Package / Case PG-TO262-3-1 TO-262-3 Long Leads, I2Pak, TO-262AA	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Mounting Type	Through Hole
	Supplier Device Package	PG-TO262-3-1
Report errors?	Package / Case	TO-262-3 Long Leads, I2Pak, TO-262AA
		Report errors?

SPI35N10 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

SPI35N10 Payment Methods



















SPI35N10 Shipping Methods













If you have any question about SPI35N10, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com